

MEMORY DEVICE WITH A FLEXIBLE REDUCED DENSITY OPTION

Abstract

5 A dynamic random access memory device is capable of converting from
a full density memory device to a reduced density memory device. The reduced
density memory device compensates for cell failures in a plurality of cell blocks,
regardless of the location of the cell failures. The memory device includes a row
address mapping fuse for selectively determining row address combinations
10 capable of storing data bits. A row address mapping logic is coupled to the row
address mapping fuse and is capable of routing data bits to the address
combinations capable of storing data bits.